MJ15003 (NPN), MJ15004 (PNP)

Complementary Silicon Power Transistors

The MJ15003 and MJ15004 are power transistors designed for high power audio, disk head positioners and other linear applications.

Features

- High Safe Operating Area (100% Tested) – 5.0 A @ 50 V
- For Low Distortion Complementary Designs
- High DC Current Gain – h_{FE} = 25 (Min) @ I_C = 5 Adc
- Pb–Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	140	Vdc
Collector–Base Voltage	V_{CBO}	140	Vdc
Emitter–Base Voltage	V_{EBO}	5	Vdc
Collector Current – Continuous	I_C	20	Adc
Base Current – Continuous	I_B	5	Adc
Emitter Current – Continuous	I_E	25	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	250 1.43	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	0.70	°C/W
Maximum Lead Temperature for Soldering Purposes 1/16″ from Case for ≤ 10 secs	T_L	265	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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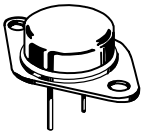
20 AMPERE
POWER TRANSISTORS
COMPLEMENTARY SILICON
140 VOLTS, 250 WATTS



TO–204AA (TO–3)
CASE 1–07
STYLE 1

MARKING DIAGRAM

MJ1500x = Device Code
x = 3 or 4
G = Pb–Free Package
A = Location Code
YY = Year
WW = Work Week
MEX = Country of Orgin

ORDERING INFORMATION

Device	Package	Shipping
MJ15003	TO–204AA	100 Units/Tray
MJ15003G	TO–204AA (Pb–Free)	100 Units/Tray
MJ15004	TO–204AA	100 Units/Tray
MJ15004G	TO–204AA (Pb–Free)	100 Units/Tray

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector Emitter Sustaining Voltage (Note 1) (I_C = 200 mAdc, I_B = 0)	$V_{CEO(sus)}$	140	–	Vdc
Collector Cutoff Current (V_{CE} = 140 Vdc, $V_{BE(off)}$ = 1.5 Vdc) (V_{CE} = 140 Vdc, $V_{BE(off)}$ = 1.5 Vdc, T_C = 150°C)	I_{CEX}	 – –	 100 2	 μAdc mAdc
Collector Cutoff Current (V_{CE} = 140 Vdc, I_B = 0)	I_{CEO}	–	250	μAdc
Emitter Cutoff Current (V_{EB} = 5 Vdc, I_C = 0)	I_{EBO}	–	100	μAdc
SECOND BREAKDOWN				
Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 50 Vdc, t = 1 s (non repetitive)) (V_{CE} = 100 Vdc, t = 1 s (non repetitive))	$I_{S/b}$	 5.0 1.0	 – –	Adc
ON CHARACTERISTICS				
DC Current Gain (I_C = 5 Adc, V_{CE} = 2 Vdc)	h_{FE}	25	150	–
Collector Emitter Saturation Voltage (I_C = 5 Adc, I_B = 0.5 Adc)	$V_{CE(sat)}$	–	1.0	Vdc
Base Emitter On Voltage (I_C = 5 Adc, V_{CE} = 2 Vdc)	$V_{BE(on)}$	–	2.0	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain — Bandwidth Product (I_C = 0.5 Adc, V_{CE} = 10 Vdc, f_{test} = 0.5 MHz)	f_T	2.0	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f_{test} = 1 MHz)	c_{ob}	–	1000	pF

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS MJ15003G (NPN)

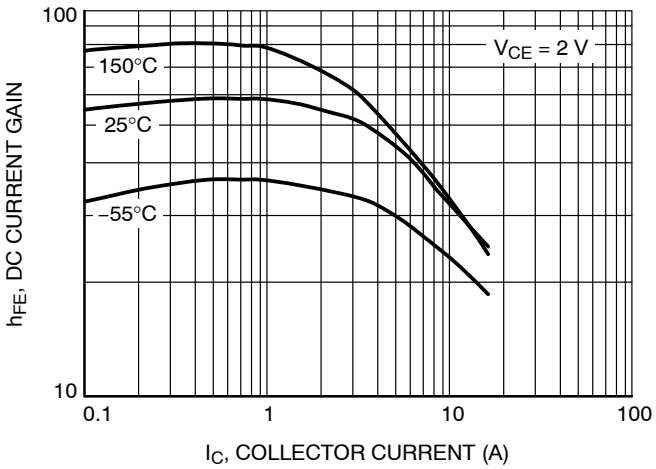


Figure 1. DC Current Gain

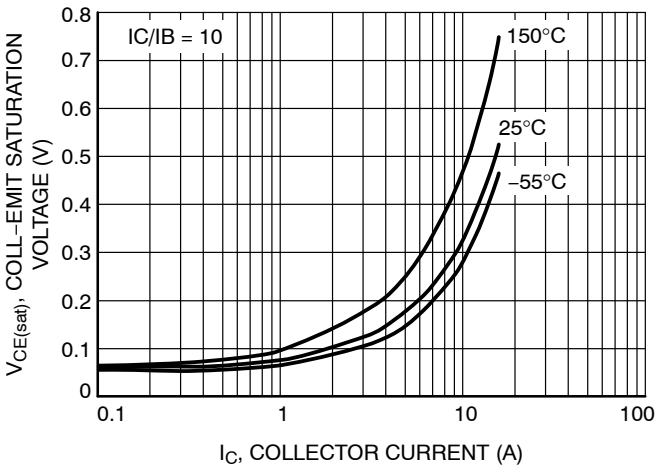


Figure 2. Collector–Emitter Saturation Voltage

TYPICAL CHARACTERISTICS MJ15003G (NPN)

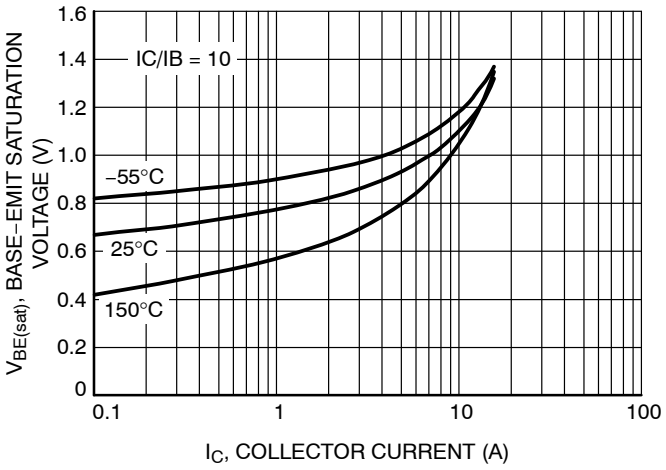


Figure 3. Base−Emitter Saturation Voltage

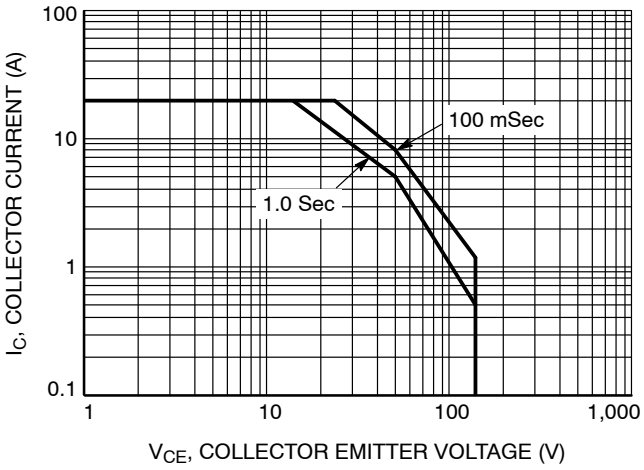


Figure 4. Safe Operating Area

TYPICAL CHARACTERISTICS MJ15004G (PNP)

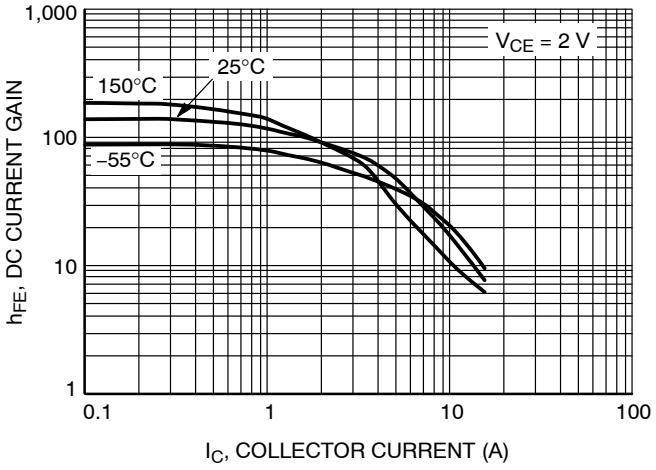


Figure 5. DC Current Gain

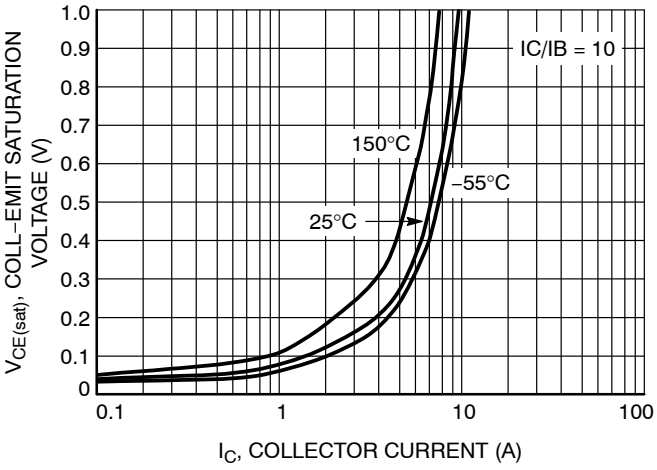


Figure 6. Collector−Emitter Saturation Voltage

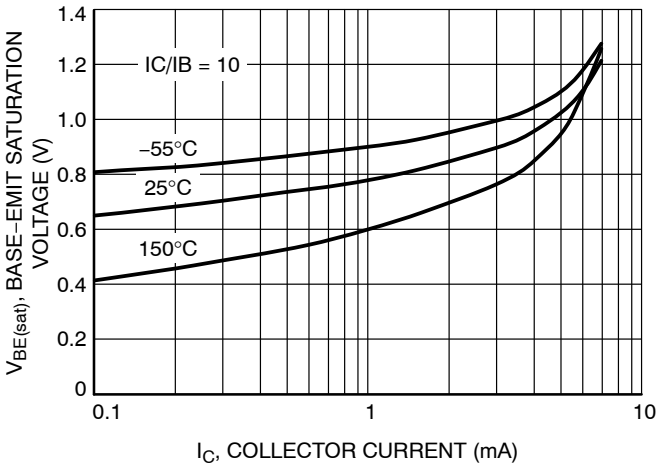


Figure 7. Base−Emitter Saturation Voltage

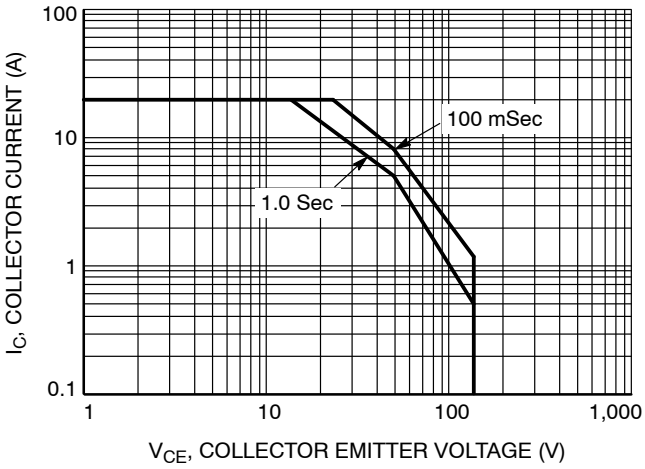
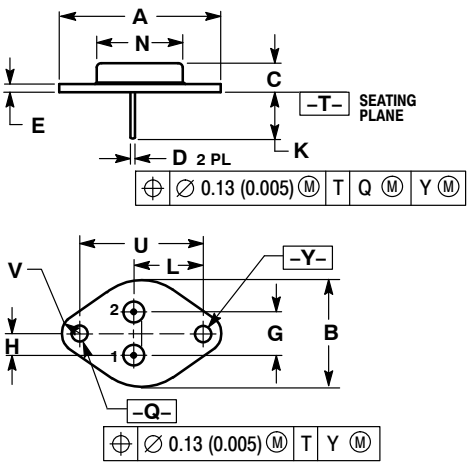


Figure 8. Safe Operating Area

PACKAGE DIMENSIONS

TO−204 (TO−3)
CASE 1−07
ISSUE Z



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO−204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
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MJ15003/D